



P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

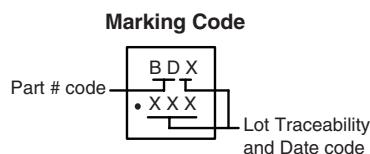
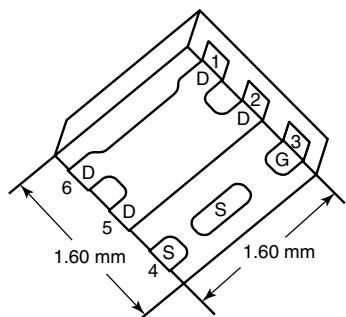
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^{a, f}	Q_g (Typ.)
- 30	0.087 at $V_{GS} = - 10$ V	- 9	3.5 nC
	0.158 at $V_{GS} = - 4.5$ V	- 7.2	

FEATURES

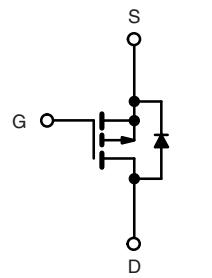
- Halogen-free
- TrenchFET® Power MOSFET
- New Thermally Enhanced PowerPAK® SC-75 Package
- Small Footprint Area

RoHS
COMPLIANT

PowerPAK SC-75-6L-Single



Ordering Information: SiB415DK-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

APPLICATIONS

- Load Switch, PA Switch and Battery Switch for Portable Devices

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	I_D	- 9 ^a	A
		- 7.7	
		- 4.17 ^{a, b}	
		- 3.36 ^{a, b}	
Pulsed Drain Current	I_{DM}	15	
Continuous Source-Drain Diode Current	I_S	- 9 ^a	W
		- 2 ^{a, b}	
Maximum Power Dissipation	P_D	13	W
		8.4	
		2.4 ^{a, b}	
		1.6 ^{a, b}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{c, d}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, e}	$t \leq 5$ s	R_{thJA}	41	51
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	7.5	9.5

Notes:

- Surface Mounted on 1" x 1" FR4 board.
- $t = 5$ s.
- See Solder Profile (<http://www.vishay.com/ppg?73257>). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under Steady State conditions is 105 °C/W.
- Based on $T_C = 25$ °C.

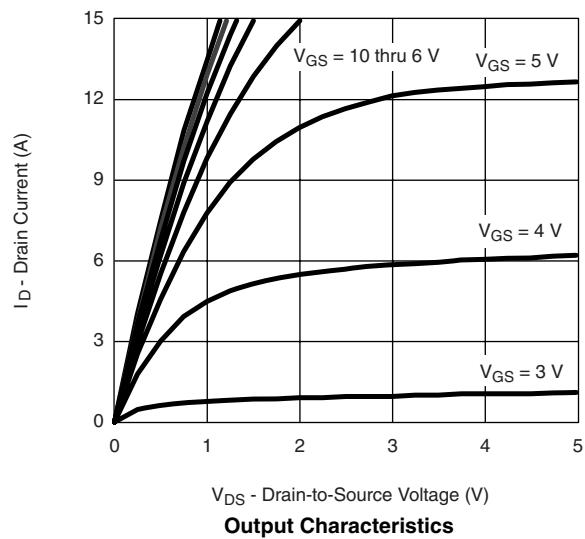
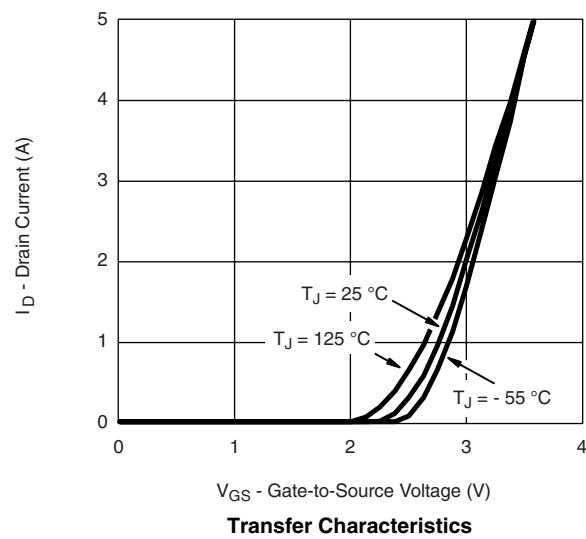
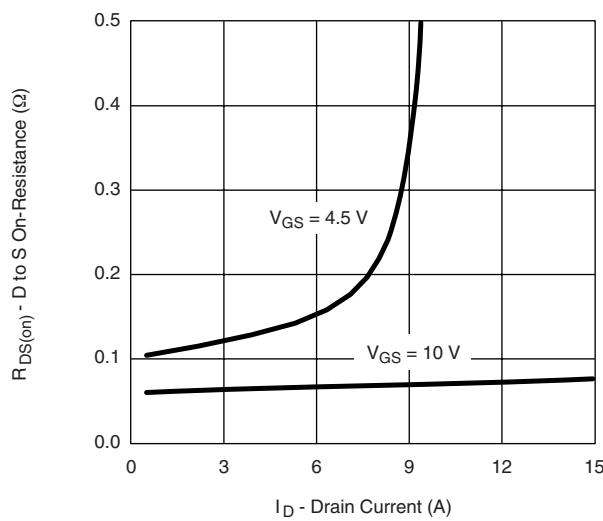
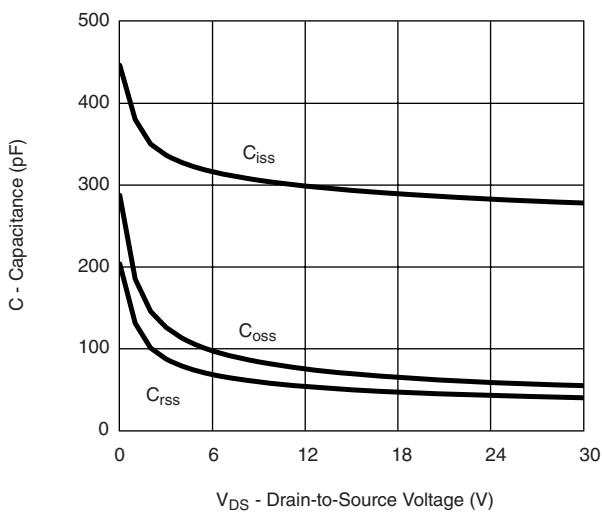
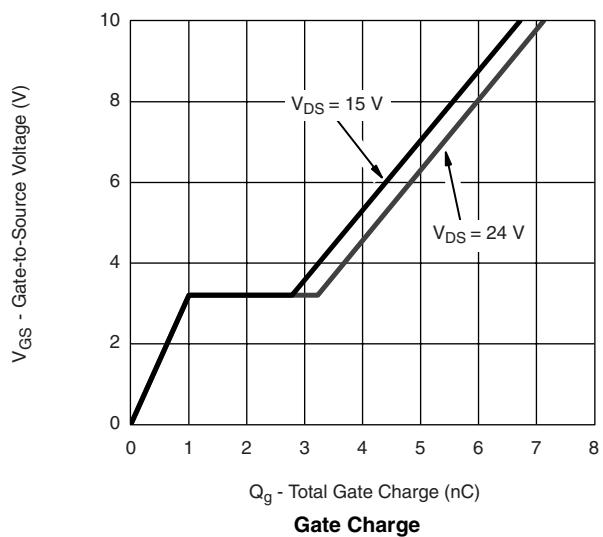
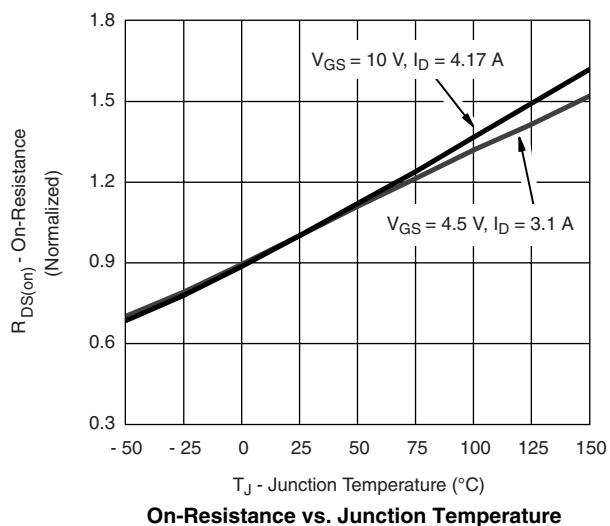
SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted

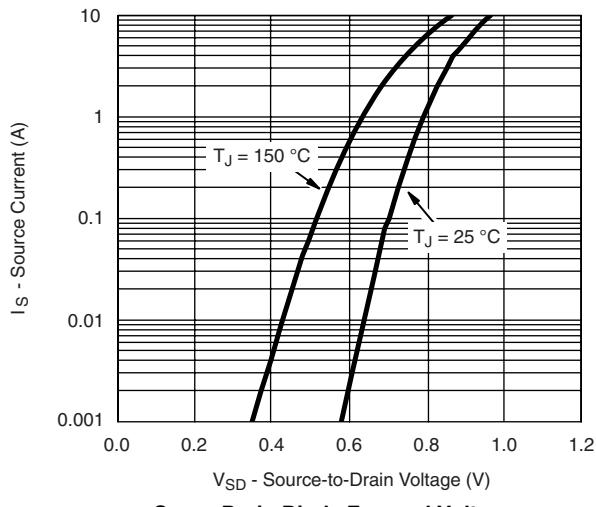
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250 \mu\text{A}$		-24.2		mV/°C
$V_{GS(\text{th})}$ Temperature Coefficient	$\Delta V_{GS(\text{th})}/T_J$			4		
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	-1		-3	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μA
		$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^\circ\text{C}$			-10	
On-State Drain Current ^a	$I_{D(\text{on})}$	$V_{DS} \leq 5 \text{ V}, V_{GS} = -10 \text{ V}$	5			A
Drain-Source On-State Resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = -10 \text{ V}, I_D = -4.17 \text{ A}$		0.072	0.087	Ω
		$V_{GS} = -4.5 \text{ V}, I_D = -3.1 \text{ A}$		0.130	0.158	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15 \text{ V}, I_D = -4.17 \text{ A}$		5.5		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		295		pF
Output Capacitance	C_{oss}			70		
Reverse Transfer Capacitance	C_{rss}			50		
Total Gate Charge	Q_g	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -4.17 \text{ A}$		6.7	10.05	nC
Gate-Source Charge	Q_{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -4.17 \text{ A}$		3.5	5.25	
Gate-Drain Charge	Q_{gd}			1		
Gate Resistance	R_g			1.78		
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = -15 \text{ V}, R_L = 6.07 \Omega$ $I_D \equiv -2.47 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$		9.4		Ω
Rise Time	t_r			43	64.5	ns
Turn-Off Delay Time	$t_{d(\text{off})}$			55	82	
Fall Time	t_f			13	19.5	
Turn-On Delay Time	$t_{d(\text{on})}$			10	15	
Rise Time	t_r			6	9	
Turn-Off Delay Time	$t_{d(\text{off})}$			8.5	12.75	
Fall Time	t_f			14	21	
				9	13.5	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25^\circ\text{C}$			-9	A
Pulse Diode Forward Current	I_{SM}				15	
Body Diode Voltage	V_{SD}	$I_S = -3.2 \text{ A}, V_{GS} = 0 \text{ V}$		-0.8	-1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -3.2 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}, T_J = 25^\circ\text{C}$		14.63	22	ns
Body Diode Reverse Recovery Charge	Q_{rr}			8	12	nC
Reverse Recovery Fall Time	t_a			9.13		ns
Reverse Recovery Rise Time	t_b			5.5		

Notes:

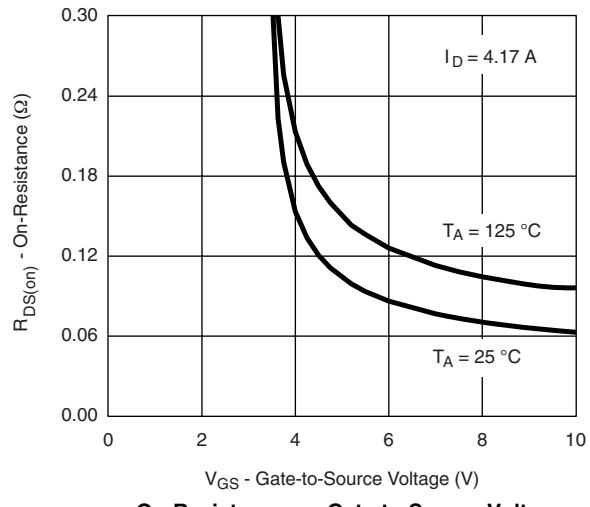
- a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

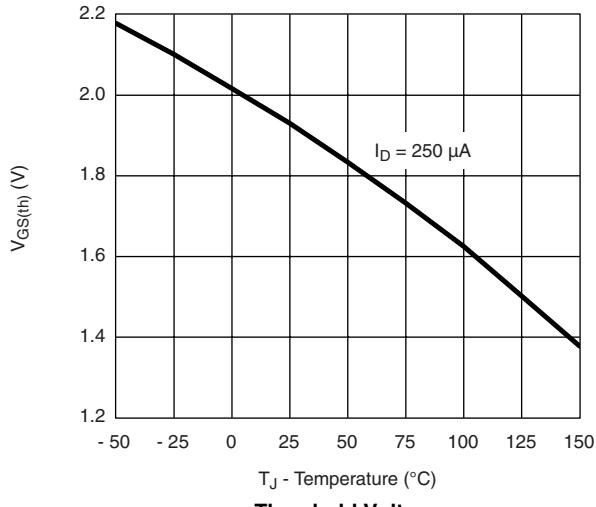
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current and Gate Voltage****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature**

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

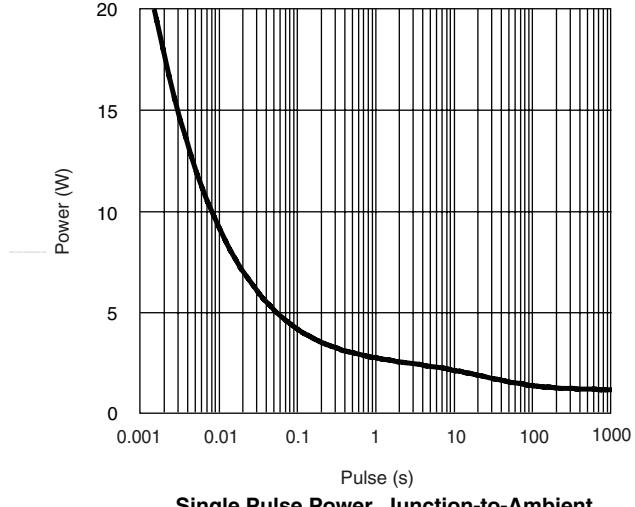
Source-Drain Diode Forward Voltage



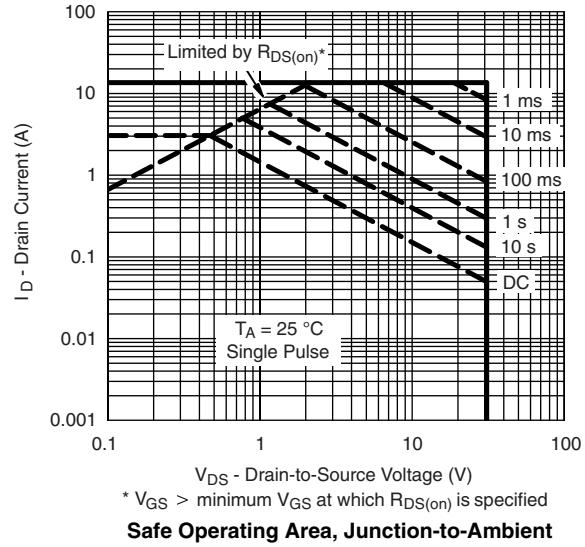
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

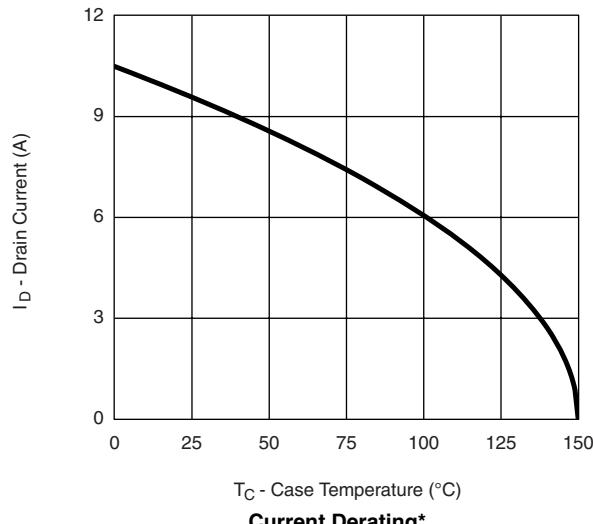


Single Pulse Power, Junction-to-Ambient

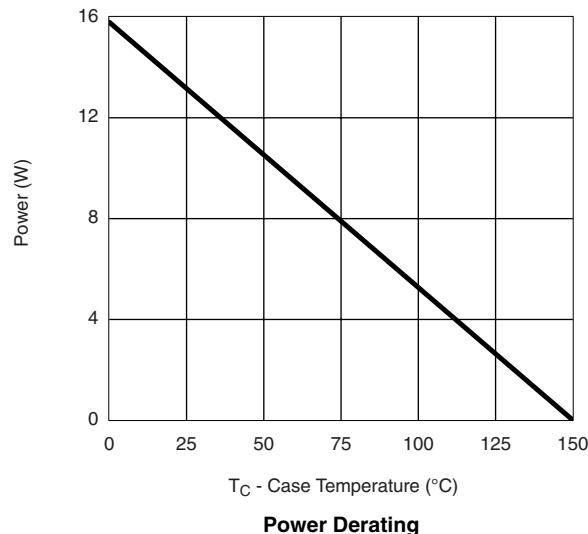


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted T_C - Case Temperature (°C)

Current Derating*

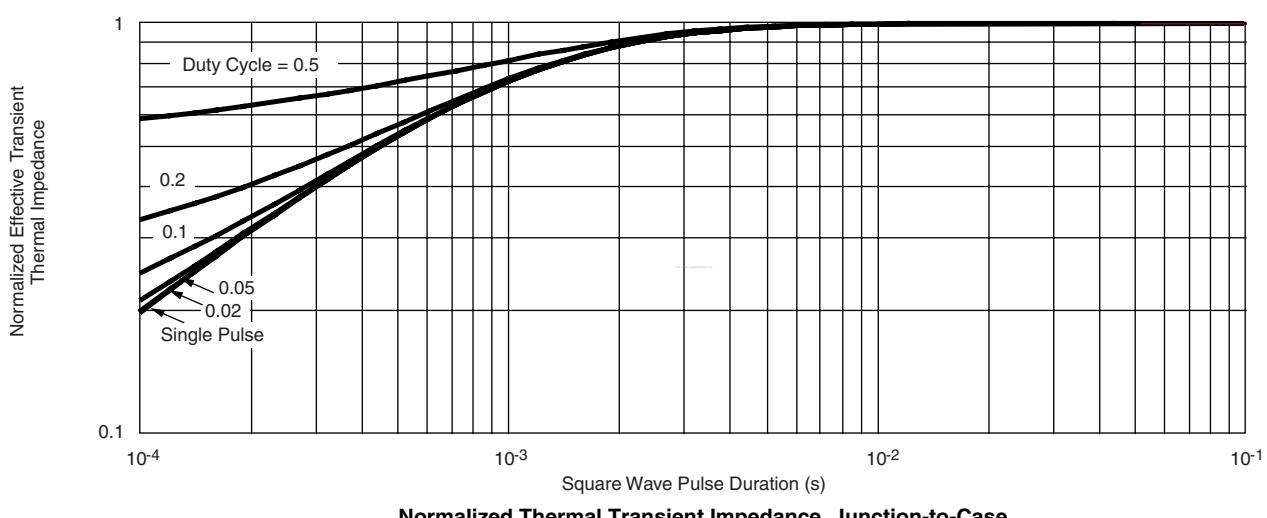
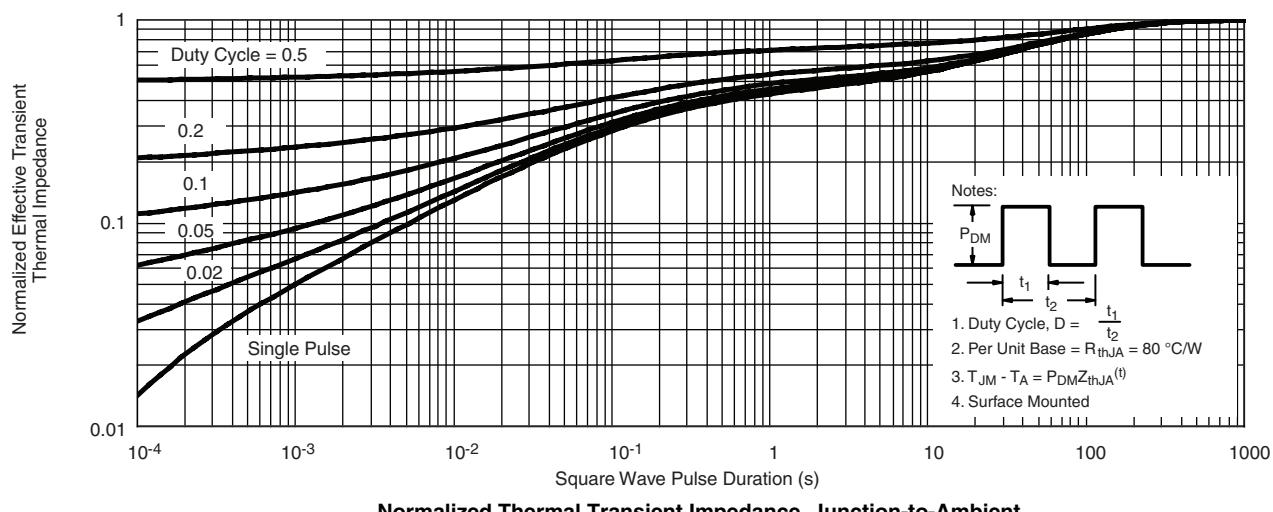
 T_C - Case Temperature (°C)

Power Derating

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

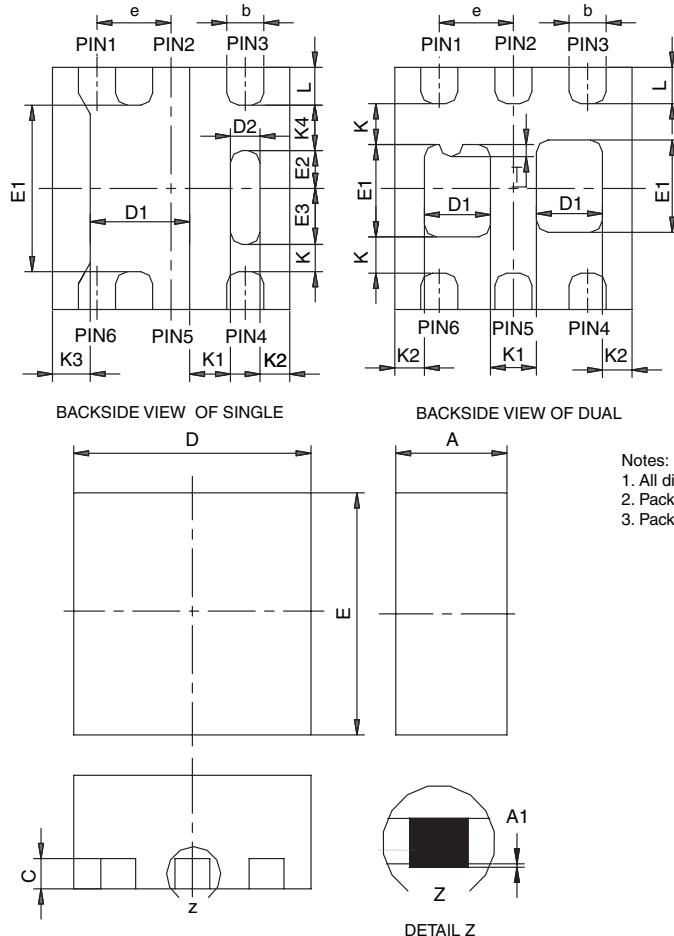
SiB415DK

Vishay Siliconix

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?70438>.

PowerPAK® SC75-6L



Notes:

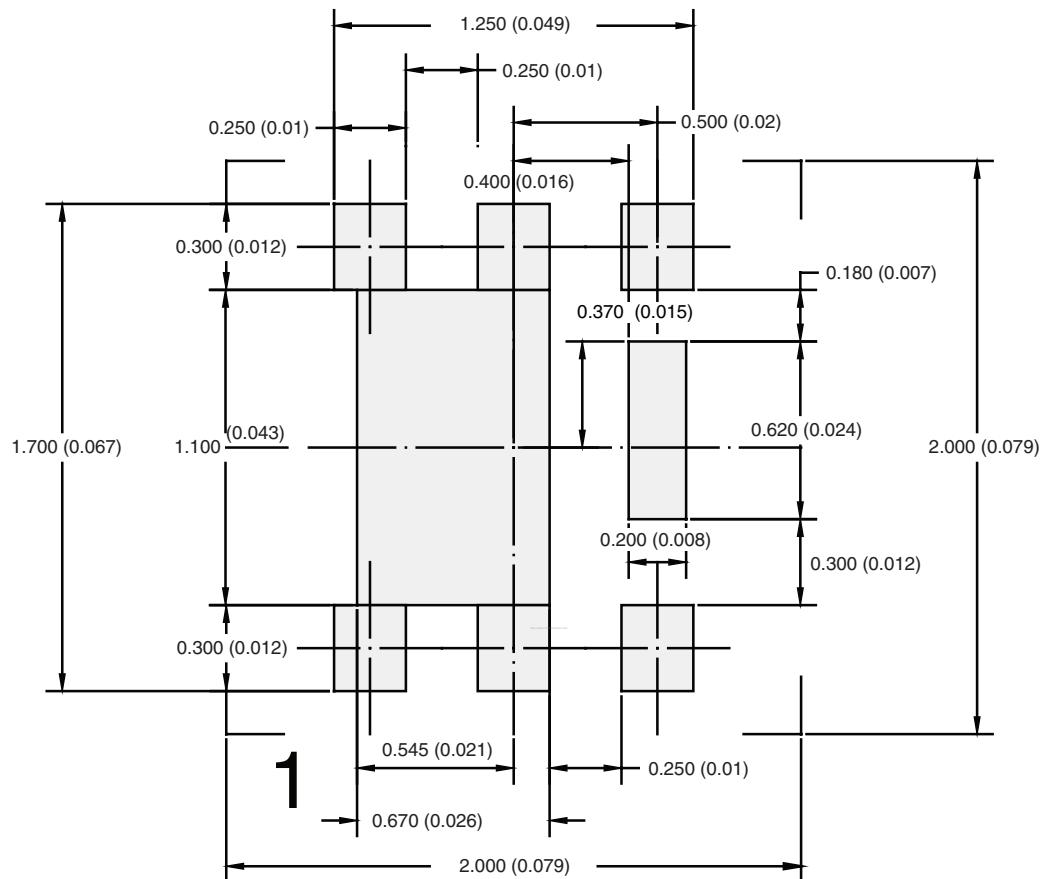
1. All dimensions are in millimeters
2. Package outline exclusive of mold flash and metal burr
3. Package outline inclusive of plating

DIM	SINGLE PAD						DUAL PAD					
	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
A	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.18	0.25	0.33	0.007	0.010	0.013	0.18	0.25	0.33	0.007	0.010	0.013
C	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
D1	0.57	0.67	0.77	0.022	0.026	0.030	0.34	0.44	0.54	0.013	0.017	0.021
D2	0.10	0.20	0.30	0.004	0.008	0.012						
E	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
E1	1.00	1.10	1.20	0.039	0.043	0.047	0.51	0.61	0.71	0.020	0.024	0.028
E2	0.20	0.25	0.30	0.008	0.010	0.012						
E3	0.32	0.37	0.42	0.013	0.015	0.017						
e	0.50 BSC			0.020 BSC			0.50 BSC			0.020 BSC		
K	0.180 TYP			0.007 TYP			0.245 TYP			0.010 TYP		
K1	0.275 TYP			0.011 TYP			0.320 TYP			0.013 TYP		
K2	0.200 TYP			0.008 TYP			0.200 BSC			0.008 TYP		
K3	0.255 TYP			0.010 TYP								
K4	0.300 TYP			0.012 TYP								
L	0.15	0.25	0.35	0.006	0.010	0.014	0.15	0.25	0.35	0.006	0.010	0.014
T							0.03	0.08	0.13	0.001	0.003	0.005

ECN: C-07431 – Rev. C, 06-Aug-07

DWG: 5935

RECOMMENDED PAD LAYOUT FOR PowerPAK® SC75-6L Single



[Return to Index](#)

APPLICATION NOTE

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